



FORM PTO-AVENUE				ATTORNEY DOCKET NO.: CIS-001CP					
SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT				APPLICANTS: Schowalter and Slack					
				SERIAL NO.: 10/822,336					
				FILING DATE: April 12, 2004					
				GROUP: 1722					
U.S. PATENT DOCUMENTS									
EXAM INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE		
RK	A1	4,234,554	11/18/80	Rabenau et al.					
RK	A2	5,858,085	01/12/1999	Arai et al.					
RK	A3	5,858,086	01/12/1999	Hunter					
RK	A4	5,909,036	06/01/1999	Tanaka et al.					
RK	A5	5,972,109	10/26/1999	Hunter					
RK	A6	6,001,748	06/04/1997	Tanaka et al.					
RK	A7	6,045,612	04/04/2000	Hunter					
RK	A8	6,048,813	04/11/2000	Hunter					
RK	A9	6,063,185	05/16/2000	Hunter					
RK	A10	6,086,672	07/11/2000	Hunter					
RK	A11	6,187,089	02/13/2001	Phillips et al.					
RK	A11	6,296,956	10/02/2001	Hunter					
FOREIGN PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
RK	B1	2000-154090	06/2000	JP				YES	N
RK	B2	02 018379A	01/22/1990	JP				YES	N
EXAMINER					DATE CONSIDERED				

FORM PTO - 1449		ATTORNEY DOCKET NO.: CIS-001CP	
SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT		APPLICANTS:	Schowalter and Slack
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		FILING DATE:	April 12, 2004
		GROUP:	1722
OTHER ART, JOURNAL ARTICLES, ETC.			
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)		
RK	C1	Dryburgh, "Estimation of maximum growth rate for aluminum nitride crystals by direct sublimation", <i>J. Crystal Growth</i> 125, 65-68 (1992).	
RK	C2	A.S. Segal S. Yu, Karpov, Yu. N. Makarov, E.N. Mokhov, A.D. Roenkov, M.G. Ramm, Yu. A. Vodakov, "On mechanisms of sublimation growth of AlN bulk crystals", <i>J. Crystal Growth</i> 211, 68-72 (2000).	
RK	C3	B. Raghothamachar, W.M. Vetter, M. Dudley, R. Dalmau, R. Schlessner, Z. Sitar, E. Michaels, and J.W. Kolis, "Synchrotron white beam topography characterization of physical vapor transport grown AlN and ammonothermal GaN", <i>J. Crystal Growth</i> 246, 271-280 (2002).	
RK	C4	R. Schlessner, R. Dalmau, and Z. Sitar, "Seeded growth of AlN bulk single crystals by sublimation", <i>J. Crystal Growth</i> 241, 416-420 (2002).	
RK	C5	L.J. Schowalter, G.A. Slack, J.B. Whitlock, K. Morgan, S.B. Schujman, B. Raghothamachar, M. Dudley, and K.R. Evans, "Fabrication of native, single-crystal AlN substrates", <i>Phys. Stat. Sol. (c)</i> , 104, (2003).	
RK	C6	V. Noveski, R. Schlessner, S. Mahajan, S. Beaudoin, and Z. Sitar, "Growth of AlN crystals on AlN/SiC seeds by AlN powder sublimation in nitrogen atmosphere", <i>MRS Internet J. Nitride Semicond. Res.</i> 9, 2 (2004).	
RK	C7	V. Noveski, R. Schlessner, S. Mahajan, S. Beaudoin, and Z. Sitar, "Mass transfer in AlN crystal growth at high temperatures", <i>J. Crystal Growth</i> 264, 369-378 (2004).	
EXAMINER		/Robert Kunemund/	DATE CONSIDERED 05/23/2006

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